

### INCHANGE SEMICONDUCTOR

## **isc** Silicon NPN Darlington Power Transistor

# 2SD929

#### DESCRIPTION

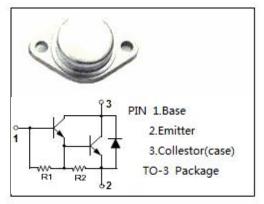
- High DC Current Gain
- : h<sub>FE</sub>= 700(Min.)@ I<sub>C</sub>= 1A, V<sub>CE</sub>= 4V
- · High Collector-Emitter Breakdown Voltage-
- : V<sub>(BR)CEO</sub> = 180V(Min)
- High Reliability
- Good Linearity of h<sub>FE</sub>
- Wide Area of Safe Operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

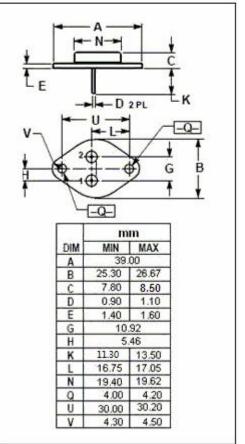
### **APPLICATIONS**

- Color & B/W TV power supply
- Active power filter
- Series regulators
- · General purpose power amplifiers

### ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	oltage 200		
V <sub>CEO</sub>	Collector-Emitter Voltage	180	V	
V <sub>EBO</sub>	Emitter-Base Voltage	V		
Ic	Collector Current-Continuous 5		А	
I <sub>B</sub>	Base Current-Continuous 0.5		А	
Pc	Collector Power Dissipation @T <sub>C</sub> =25°C	80	W	
Tj	Junction Temperature	150	°C	
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C	





isc website: <u>www.iscsemi.com</u>



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### **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0	180			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 1mA; I <sub>B</sub> = 0	200			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 3mA; I <sub>C</sub> = 0	6			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1.5A ,I <sub>B</sub> = 50mA			1.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 1.5A ,I <sub>B</sub> = 50mA			2.0	V
Ісво	Collector Cutoff current	V <sub>CB</sub> = 200V, I <sub>E</sub> = 0			0.1	mA
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 180V, I <sub>B</sub> = 0			0.5	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			3	mA
hfe	DC Current Gain	I <sub>C</sub> = 1A ; V <sub>CE</sub> = 4V	700		20000	

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